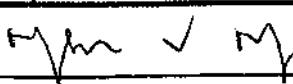


INFORMATION DISCLOSURE CITATION <i>(Use several sheets if necessary)</i>			Docket Number (Optional): FIS920030371US1		Application Number: 10/708,378		
			Applicant(s): Zhu, et al.		Filing Date: 2-27-04		
					Group Art Unit: 2818		
U.S. PATENT DOCUMENTS							
*EXAMINER INITIALS	REF	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILED DATE IF APPROPRIATE
WJ		5,683,934	11-4-97	Candelaria			
		5,840,593	11-24-98	Leedy			
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WJ		5,940,716	8-17-99	Jin, et al.			
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FOREIGN PATENT DOCUMENTS							
	REF	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	Transliteration YES NO
OTHER DOCUMENTS <i>(Including Author, Title, Date, Pertinent Pages, Etc.)</i>							
WJ		S.R. Sheng, et al., "Degradation and Recovery of SiGe HBTs Following Radiation and Hot-Carrier Stressing." Pp. 14-15. Date is not available.					
WJ		Z. Yang, et al., "Avalanche Current Induced Hot Carrier Degradation in 200 GHz SiGe Heterojunction Bipolar Transistors." Pp. 1-5. Date is not available.					
EXAMINER			DATE CONSIDERED 8-15-05				
EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP Section 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.							

INFORMATION DISCLOSURE CITATION <i>(Use several sheets if necessary)</i>				Docket Number (Optional) PIS920030371US1		Application Number 10/708,378	
				Applicant(s) Zhu, et al.			
				Filing Date 2-27-04		Group Art Unit 2818	
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NP		5,571,741	11-5-96	Leedy			
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		5,670,798	9-23-97	Schetzina			
NP		5,679,965	10-21-97	Schetzina			
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*EXAMINER INITIAL	REF	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
FOREIGN PATENT DOCUMENTS							
	REF	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	Translation
							YES
							NO
OTHER DOCUMENTS <i>(Including Author, Title, Date, Pertinent Pages, Etc.)</i>							
NP		H.S. Momose, et al., "Temperature Dependence of Emitter-Base Reverse Stress Degradation and its Mechanism Analyzed by MOS Structures." Paper 6.1, pp. 140-143, IEEE, 1969					
NP		C.J. Huang, et al., "Temperature Dependence and Post-Stress Recovery of Hot Electron Degradation Effects in Bipolar Transistors." IEEE 1991 Bipolar Circuits and Technology Meeting 7.5, pp. 170-173.					
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